

ABSTRACT

Capacitors of semiconductor devices and methods of fabricating the same are disclosed. An example capacitor-fabricating method comprises: forming a first insulating layer by nitrifying a semiconductor substrate; forming a second insulating layer by depositing a transition element on the first insulating layer and performing a reoxidation process; forming a third insulating layer by nitrifying the second insulating layer using a forming gas; and forming a conducting layer on top of the third insulating layer.